

Silicon NPN Power Transistors

2SC867

DESCRIPTION

- With TO-66 package
- High collector-base breakdown voltage
: $V_{CBO}=400V(\text{min})$

APPLICATIONS

- For high voltage and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

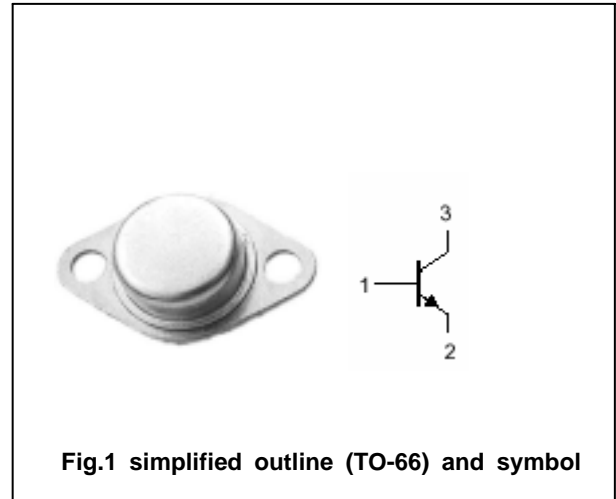


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings($T_a=$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	400	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1	A
I_{CM}	Collector current-peak		2	A
P_D	Total power dissipation	$T_C=25$	23	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =30mA; I _B =0	150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A; I _B =0.2 A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1A; I _B =0.2 A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =400V; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =0.1A ; V _{CE} =3V	50			
f _T	Transition frequency	I _C =0.2A ; V _{CE} =10V		8		MHz

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PACKAGE OUTLINE

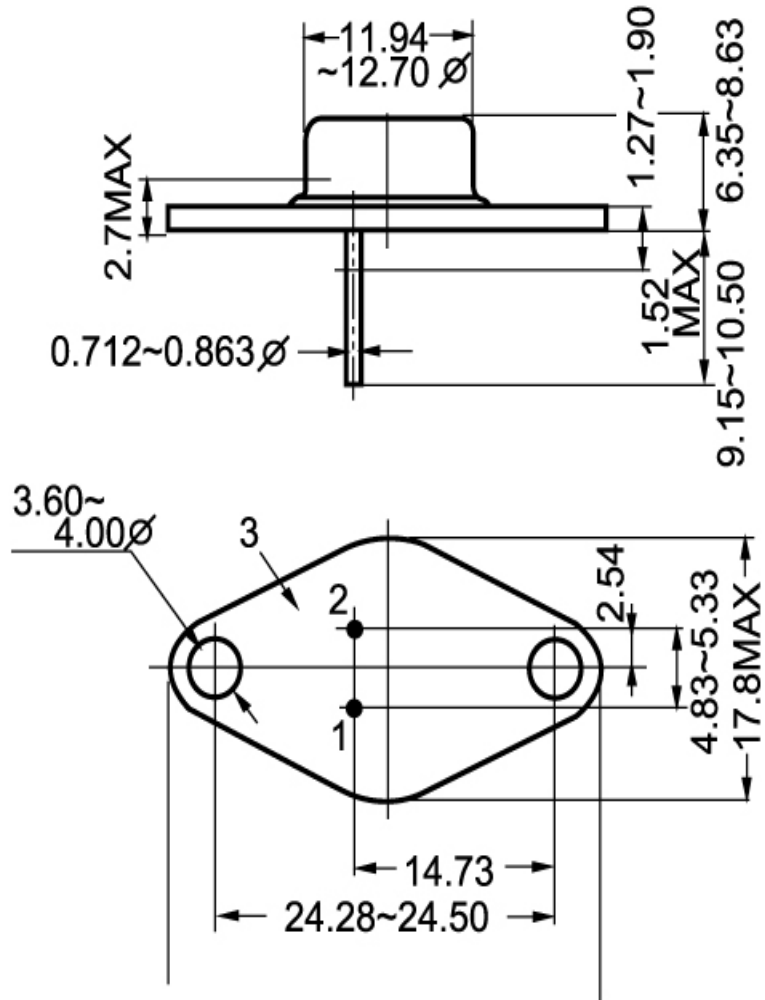


Fig.2 outline dimensions